

Electronic Supplementary Information (ESI)

Layer-number dependent and structural defects related optical properties of InSe

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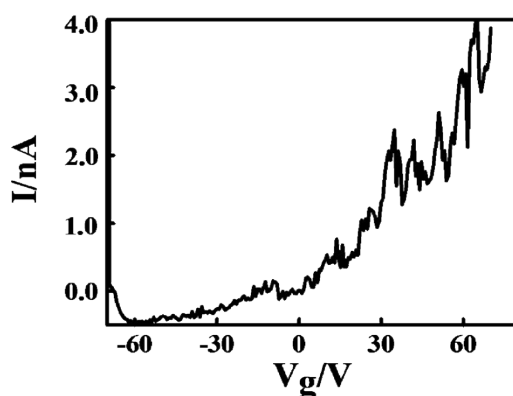


Fig. ESI1. The back-gate transfer curves of bulk InSe FET, which confirm InSe is n-doped.

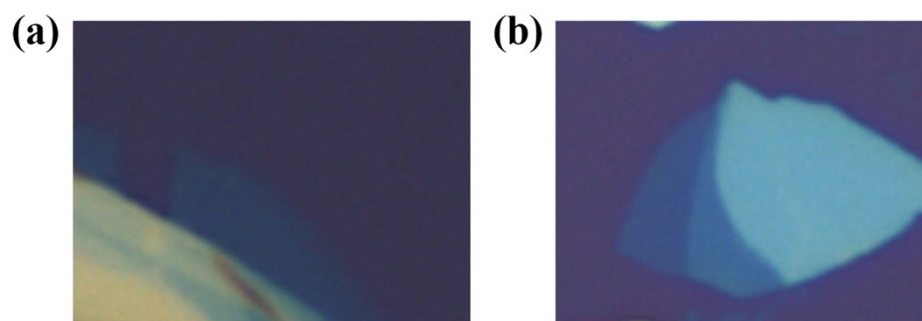


Fig. ESI2. Optical images of 4-layer (a) and 5-layer (b) InSe films.